Record Nr.	UNINA9910437909903321
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Titolo	High-Performance D/A-Converters [[electronic resource] ] : Application to Digital Transceivers / / by Martin Clara
Pubbl/distr/stampa	Berlin, Heidelberg : , : Springer Berlin Heidelberg : , : Imprint : Springer, , 2013
ISBN	1-283-94626-2
	3-642-31229-2
Edizione	[1st ed. 2013.]
Descrizione fisica	1 online resource (296 p.)
Collana	Springer Series in Advanced Microelectronics, , 1437-0387 ; ; 36
Disciplina	621.38159
Soggetti	Signal processing
	Image processing
	Speech processing systems
	Electronics
	Microelectronics
	Semiconductors
	Electronic circuits
	Signal, image and Speech Flocessing
	Electronic Circuits and Devices
Lingua di pubblicazione	
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Performance Figures of D/A-Converters Static Linearity Dynamic Linearity Noise-shaped D/A-Converters Advanced Current Calibration.
Sommario/riassunto	This book deals with modeling and implementation of high performance, current-steering D/A-converters for digital transceivers in nanometer CMOS technology. In the first part, the fundamental performance limitations of current-steering DACs are discussed. Based on simplified models, closed-form expressions for a number of basic non-ideal effects are derived and tested. With the knowledge of basic performance limits, the converter and system architecture can be optimized in an early design phase, trading off circuit complexity,

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silicon area and power dissipation for static and dynamic performance. The second part describes four different current-steering DAC designs in standard 130 nm CMOS. The converters have a resolution in the range of 12-14 bits for an analog bandwidth between 2.2 MHz and 50 MHz and sampling rates from 100 MHz to 350 MHz. Dynamic-Element-Matching (DEM) and advanced dynamic current calibration techniques are employed to minimize the required silicon area.